BUH1015
BUH1015HI

SGS-THOMSON MICROELECTRONICS

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPES
- HIGH VOLTAGE CAPABILITY
- VERY HIGH SWITCHING SPEED

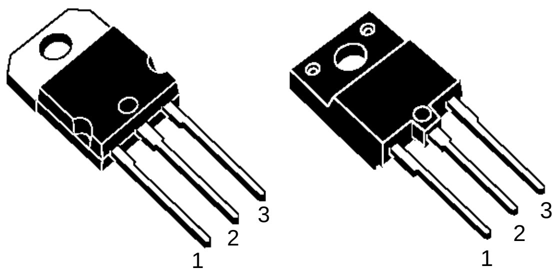
APPLICATIONS:

- HORIZONTAL DEFLECTION FOR COLOUR TV AND MONITORS

DESCRIPTION

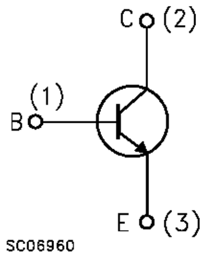
The BUH1015and BUH1015HI are manufactured using Multiepitaxial Mesa technology for cost-effective high performance and uses a Hollow Emitter structure to enhance switching speeds.

The BUH series is designed for use in horizontal deflection circuits in televisions and monitors.



TO-218 **ISOWATT218**

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	1500		V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	700		V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	10		V
I_C	Collector Current	14		A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	18		A
I_B	Base Current	8		A
I_{BM}	Base Peak Current ($t_p < 5$ ms)	11		A
P_{tot}	Total Dissipation at $T_c = 25\ ^oC$	160	70	W
T_{stg}	Storage Temperature	-65 to 150		^oC
T_j	Max. Operating Junction Temperature	150		^oC

THERMAL DATA

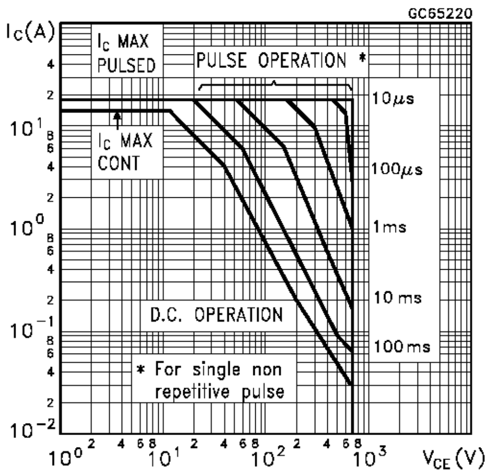
			TO-218	ISOWATT218	
$R_{thj-case}$	Thermal Resistance Junction-case	Max	0.78	1.8	$^oC/W$

ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

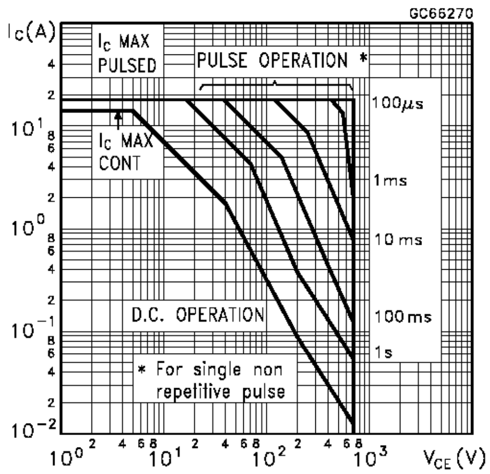
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current (V_{BE} = 0)	V_{CE} = 1500 V V_{CE} = 1500 V T_j = 125 ^oC			1 2	mA mA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{EB} = 5 V			100	μA
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	I_C = 100 mA	700			V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	I_E = 10 mA	10			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 10 A I_B = 2 A			1.5	V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 10 A I_B = 2 A			1.5	V
h_{FE}*	DC Current Gain	I_C = 10 A V_{CE} = 5 V I_C = 10 A V_{CE} = 5 V T_j = 100 ^oC	7 5	10	14	
t_s t_f	RESISTIVE LOAD Storage Time Fall Time	V_{CC} = 400 V I_C = 10 A I_{B1} = 2 A I_{B2}= -6 A		1.5 110		μs ns
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 10 A f = 31250 Hz I_{B1} = 2 A I_{B2} = -6 A $V_{ceflyback} = 1200 \sin\left(\frac{\pi}{5} 10^6\right) t$ V		4 220		μs ns
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 6 A f = 64 KHz I_{B1} = 1 A V_{beoff} = - 2 V $V_{ceflyback} = 1100 \sin\left(\frac{\pi}{5} 10^6\right) t$ V		3.7 200		μs ns

∗ Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

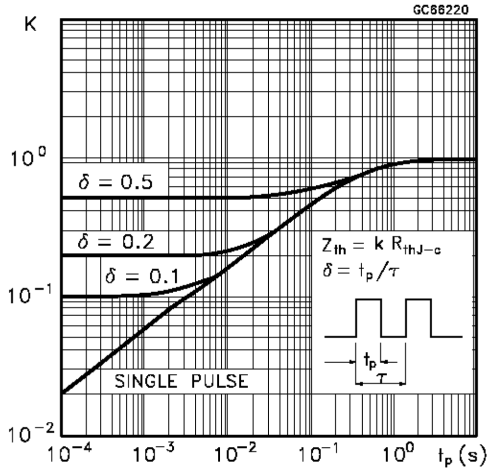
Safe Operating Area For TO-218



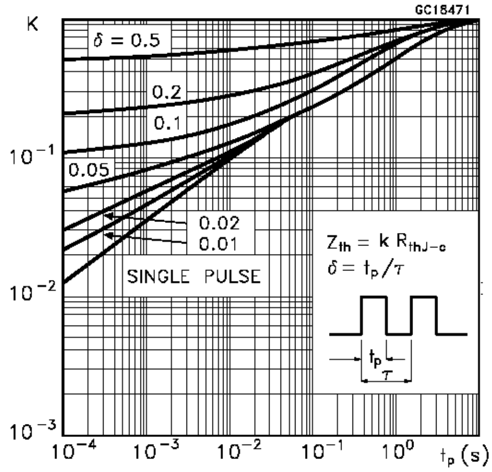
Safe Operating Area For ISOWATT218



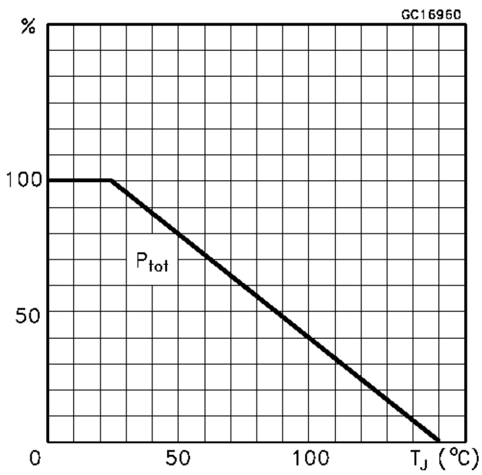
Thermal Impedance for TO-218



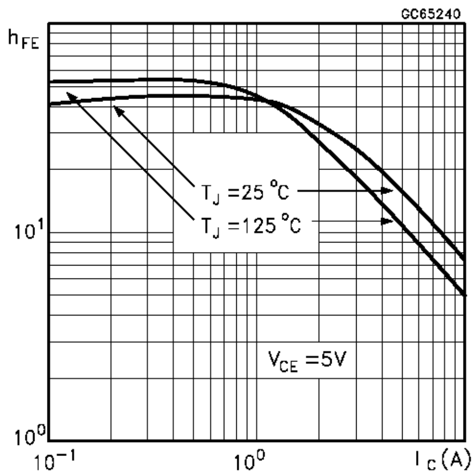
Thermal Impedance for ISOWATT218



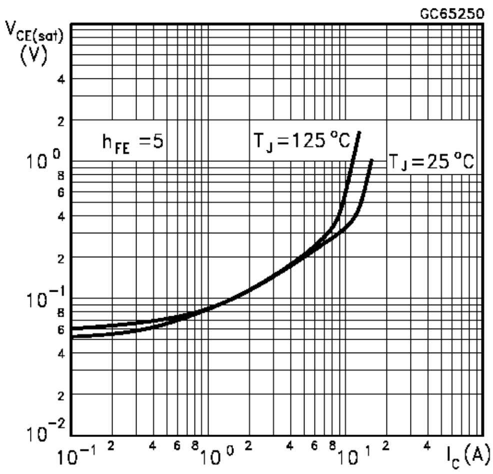
Derating Curve



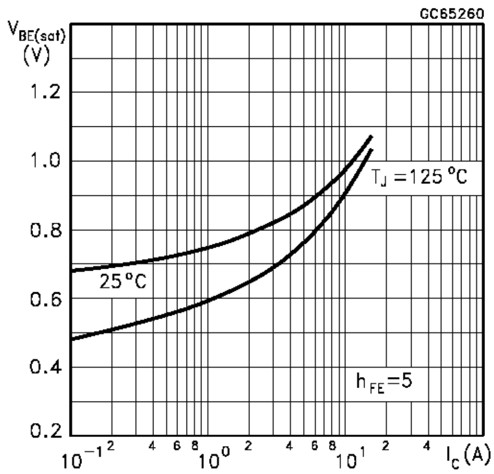
DC Current Gain



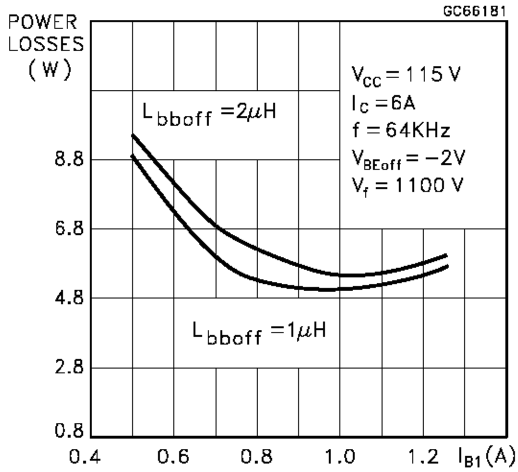
Collector Emitter Saturation Voltage



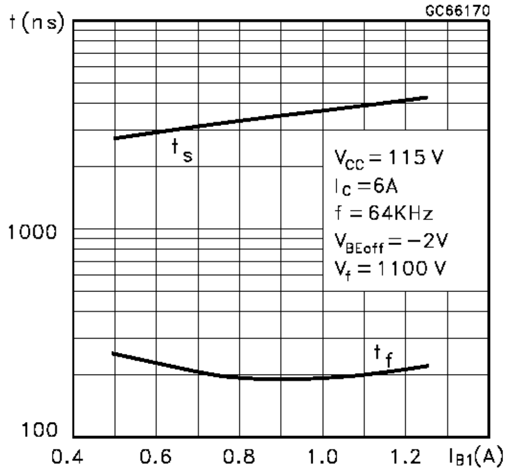
Base Emitter Saturation Voltage



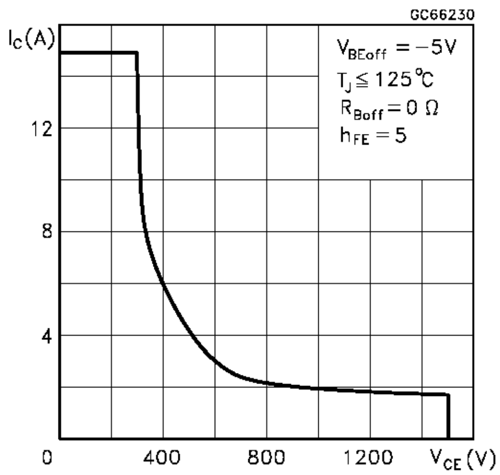
Power Losses at 64 KHz



Switching Time Inductive Load at 64KHz (see figure 2)



Reverse Biased SOA



BASE DRIVE INFORMATION

In order to saturate the power switch and reduce conduction losses, adequate direct base current I_{B1} has to be provided for the lowest gain h_{FE} at T_j = 100 °C (line scan phase). On the other hand, negative base current I_{B2} must be provided the transistor to turn off (retrace phase). Most of the dissipation, especially in the deflection application, occurs at switch-off so it is essential to determine the value of I_{B2} which minimizes power losses, fall time t_f and, consequently, T_j. A new set of curves have been defined to give total power losses, t_s and t_f as a function of I_{B1} at 64 KHz scanning frequencies for choosing the optimum drive. The test circuit is illustrated in figure 1.

The values of L and C are calculated from the following equations:

$$\frac{1}{2} L\,(I_C)^2 = \frac{1}{2} C\,(V_{CEfly})^2$$

$$\omega = 2\,\pi f = \frac{1}{\sqrt{L\,C}}$$

Where I_C= operating collector current, V_{CEfly}= flyback voltage, f= frequency of oscillation during retrace.

Figure 1: Inductive Load Switching Test Circuits.

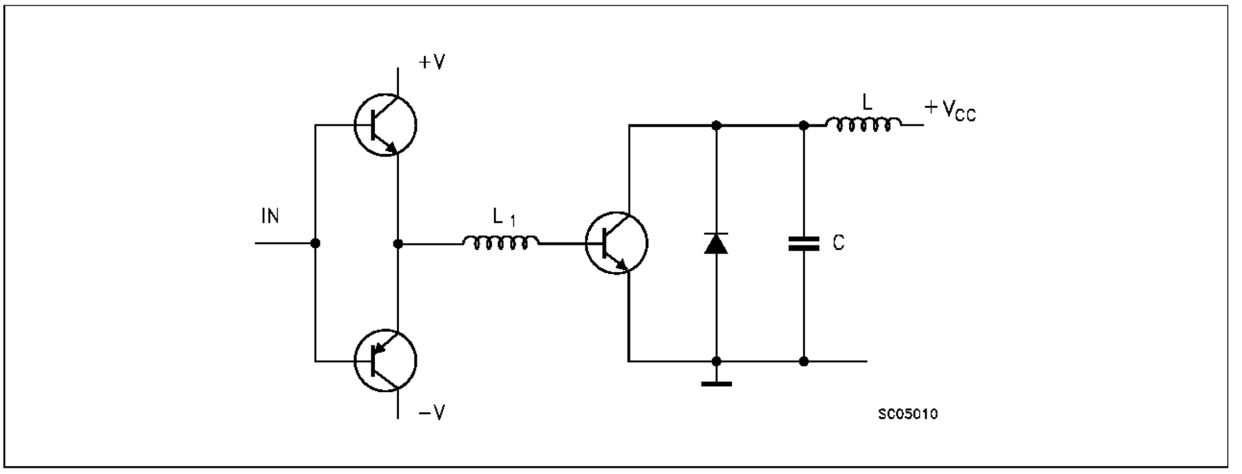
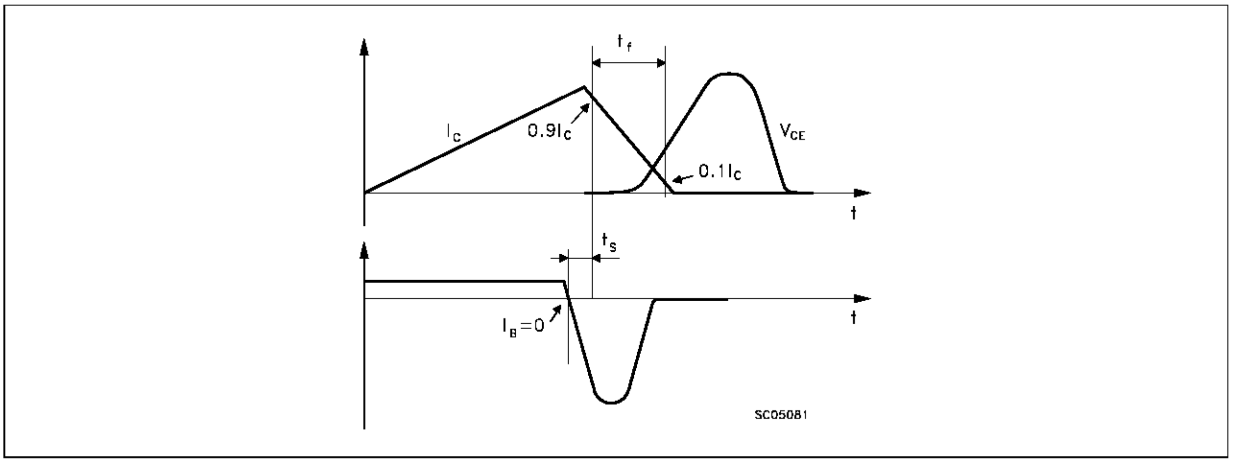
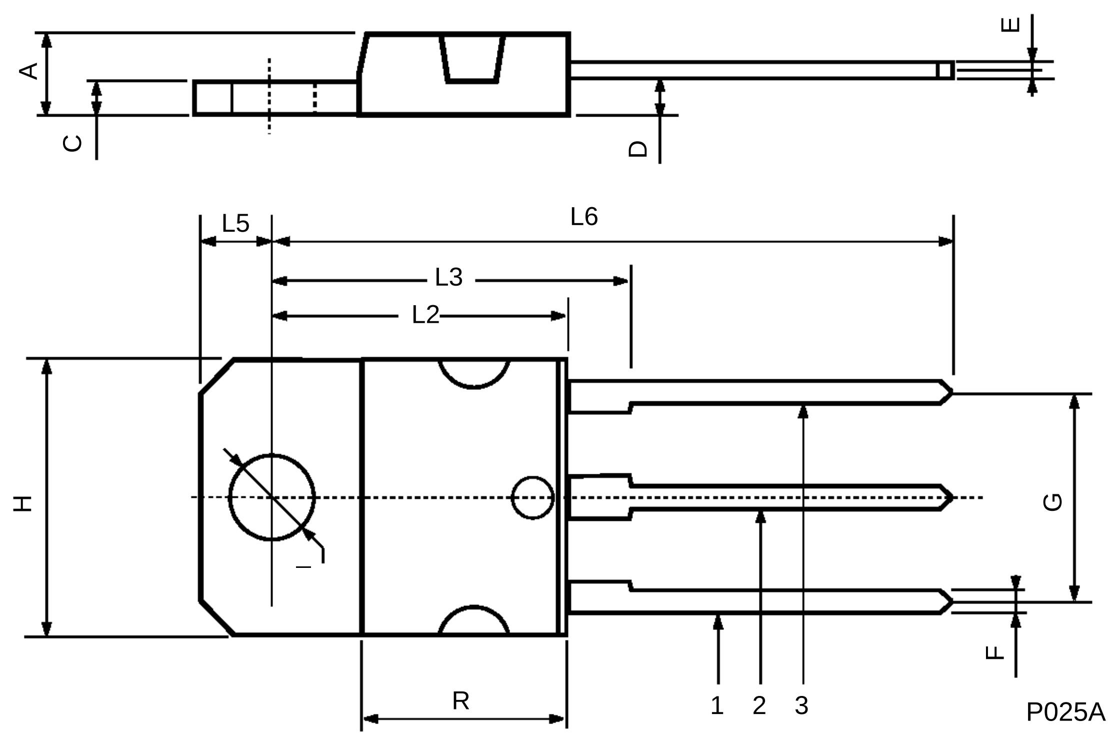


Figure 2: Switching Waveforms in a Deflection Circuit



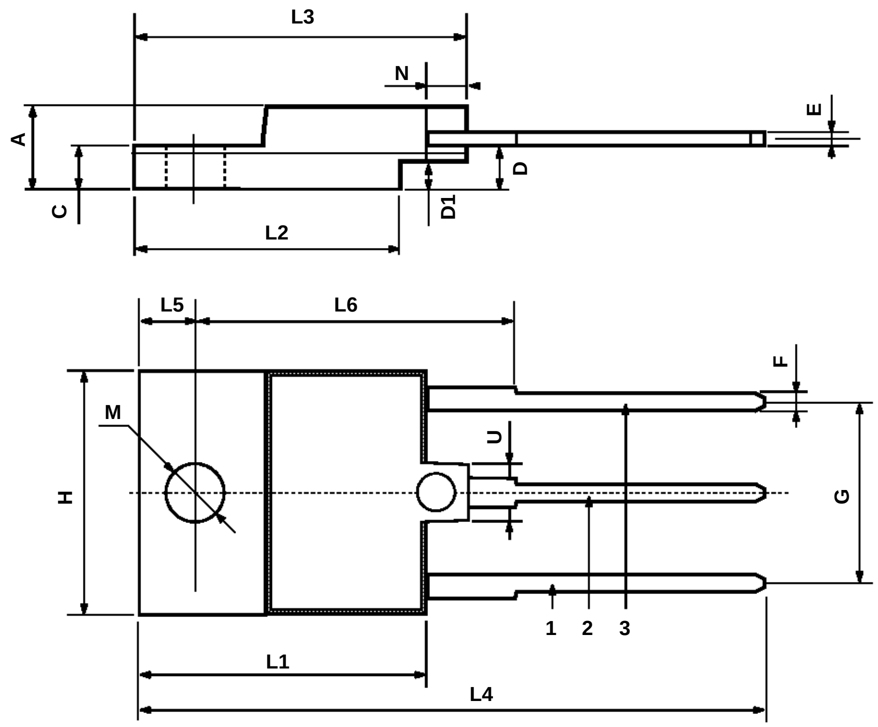
TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		4.9	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.5			0.098	
E	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
H	14.7		15.2	0.578		0.598
L2	–		16.2	–		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	–		12.2	–		0.480
Ø	4		4.1	0.157		0.161



ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.75		1	0.029		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	



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